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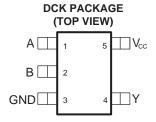
Low-Power Single 2-Input Positive-AND Gate

Check for Samples: SN74AUP1G08-Q1

FEATURES

- **AEC-Q100 Qualified with the Following** Results:
 - Device Temperature Grade 1: -40°C to 125°C Ambient Operating Temperature
 - Device HBM ESD Classification Level H2
 - Device CDM ESD Classification Level C3B
- Available in the Texas Instruments NanoStar™ **Package**
- **Low Static-Power Consumption:** $I_{CC} = 0.9 \mu A Max$
- Low Dynamic-Power Consumption: C_{pd} = 4.3 pF Typ at 3.3 V
- Low Input Capacitance: C_i = 1.5 pF Typ
- Low Noise: Overshoot and Undershoot < 10% of V_{CC}
- I_{off} Supports Partial-Power-Down Mode Operation
- **Schmitt-Trigger Action Allows Slow Input Transition and Better Switching Noise** Immunity at the Input ($V_{hys} = 250 \text{ mV}$, Typ at 3.3 V)

- Wide Operating V_{CC} Range of 0.8 V to 3.6 V
- **Optimized for 3.3-V Operation**
- 3.6-V Input/Output (I/O) Tolerant to Support **Mixed-Mode Signal Operation**
- t_{pd} = 4.3 ns Max at 3.3 V
- Suitable for Point-to-Point Applications
- Latch-Up Performance Exceeds 100 mA Per JESD-78, Class II



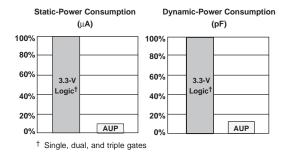
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TEXAS INSTRUMENTS

DESCRIPTION

The AUP family is Tl's premier solution to the low-power needs of the industry in battery-powered portable applications. This family ensures a very low static- and dynamic-power consumption across the entire V_{CC} range of 0.8 V to 3.6 V, resulting in increased battery life (see Figure 1). This product also maintains excellent signal integrity (see the very low undershoot and overshoot characteristics shown in Figure 2).



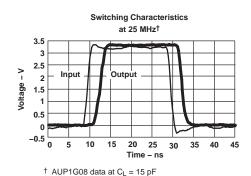


Figure 1. AUP – The Lowest-Power Family

Figure 2. Excellent Signal Integrity

This single 2-input positive-AND gate performs the Boolean function: $Y = A \bullet B$ or $Y = \overline{A} + \overline{B}$ in positive logic.

NanoStar package technology is a major breakthrough in integrated circuit (IC) packaging concepts, because it uses the die as the package.

This device is fully specified for partial-power-down applications using I_{off}. The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

ORDERING INFORMATION(1)

T _A	ORDERABLE PART NUMBER (2)	TOP-SIDE MARKING
-40°C to 125°C	SN74AUP1G08QDCKRQ1	SIT

⁽¹⁾ For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI web site at www.ti.com.

(2) Package drawings, thermal data, and symbolization are available at www.ti.com/packaging.

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FUNCTION TABLE

INP	UTS	OUTPUT
Α	В	Υ
L	L	L
L	Н	L
Н	L	L
Н	Н	Н

LOGIC DIAGRAM (POSITIVE LOGIC)



ABSOLUTE MAXIMUM RATINGS(1)

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V _{CC}	Supply voltage range		-0.5	4.6	V
VI	Input voltage range ⁽²⁾		-0.5	4.6	V
Vo	Voltage range applied to any output in the	high-impedance or power-off state ⁽²⁾	-0.5	4.6	V
Vo	Output voltage range in the high or low sta	ate ⁽²⁾	-0.5	V _{CC} + 0.5	V
I _{IK}	Input clamp current	V _I < 0		-50	mA
lok	Output clamp current	V _O < 0		-50	mA
lo	Continuous output current	•		±20	mA
	Continuous current through V _{CC} or GND			±50	mA
T _{stg}	Storage temperature range		-65	150	°C
ESD	Human body model (HBM) AEC-Q100 class	ssification level H2		2	kV
ratings	Charged device model (CDM) AEC-Q100	classification level C3B		750	V

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

THERMAL INFORMATION

	TUEDMAL METDIO(1)	SN74AUP1G08-Q1		
	THERMAL METRIC ⁽¹⁾	DCK (5 PINS)	UNIT	
θ_{JA}	Junction-to-ambient thermal resistance	304.7		
θ_{JCtop}	Junction-to-case (top) thermal resistance	115.3		
θ_{JB}	Junction-to-board thermal resistance	80.3	00/14/	
Ψ_{JT}	Junction-to-top characterization parameter	3.5	°C/W	
ΨЈВ	Junction-to-board characterization parameter	79.4		
θ_{JCbot}	Junction-to-case (bottom) thermal resistance	N/A		

(1) For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.

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Product Folder Links: SN74AUP1G08-Q1

⁽²⁾ The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.

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RECOMMENDED OPERATING CONDITIONS⁽¹⁾

			MIN	MAX	UNIT
V _{CC}	Supply voltage		0.8	3.6	V
		V _{CC} = 0.8 V	V _{CC}		
.,	High level input valtage	$V_{CC} = 1.1 \text{ V to } 1.95 \text{ V}$	0.65 × V _{CC}		V
V _{IH}	Supply voltage High-level input voltage Low-level input voltage Input voltage Output voltage High-level output current	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.6		V
		$V_{CC} = 3 \text{ V to } 3.6 \text{ V}$	V _{CC} V 0.65 × V _{CC} 1.6 2 V 0 0 0 0 0		
		$V_{CC} = 0.8 \text{ V}$		0	
.,	Laur laural imputuraltana	$V_{CC} = 1.1 \text{ V to } 1.95 \text{ V}$		$0.35 \times V_{CC}$	V
V_{IL}	Low-level input voltage	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		0.7	V
		$V_{CC} = 3 \text{ V to } 3.6 \text{ V}$		0.9	
VI	Input voltage		0	3.6	V
Vo	Output voltage		0	V_{CC}	V
		V _{CC} = 0.8 V		-20	μΑ
		V _{CC} = 1.1 V		-1.1	
	High lovel output ourrent	$V_{CC} = 1.4 \text{ V}$		-1.7	
I _{OH}	nigii-level output current	V _{CC} = 1.65		-1.9	mA
		$ \begin{array}{c} V_{CC} = 3 \ V \ to \ 3.6 \ V \\ V_{CC} = 0.8 \ V \\ V_{CC} = 1.1 \ V \ to \ 1.95 \ V \\ V_{CC} = 2.3 \ V \ to \ 2.7 \ V \\ V_{CC} = 3 \ V \ to \ 3.6 \ V \\ \hline V_{CC} = 3 \ V \ to \ 3.6 \ V \\ \hline V_{CC} = 3 \ V \ to \ 3.6 \ V \\ \hline V_{CC} = 3 \ V \ to \ 3.6 \ V \\ \hline V_{CC} = 1.1 \ V \\ \hline V_{CC} = 1.4 \ V \\ \hline V_{CC} = 2.3 \ V \\ \hline V_{CC} = 3 \ V \\ \hline V_{CC} = 1.1 \ V \\ \hline V_{CC} = 1.4 \ V \\ \hline V_{CC} = 1.65 \ V \\ \hline V_{CC} = 2.3 \ V \\ \hline V_{CC} = 2.3 \ V \\ \hline V_{CC} = 1.4 \ V \\ \hline V_{CC} = 1.4 \ V \\ \hline V_{CC} = 1.4 \ V \\ \hline V_{CC} = 2.3 \ V \\ \hline V_{CC} = 2.3 \ V \\ \hline V_{CC} = 2.3 \ V \\ \hline V_{CC} = 3 \ V \\ \hline \end{array}$	-3.1		
		$V_{CC} = 3 V$		3.6 0 0.35 × V _{CC} 0.7 0.9 3.6 V _{CC} -20 -1.1 -1.7 -1.9 -3.1 -4 20 1.1 1.7 1.9 3.1 4 200	
		$V_{CC} = 0.8 \text{ V}$		20	μA
		V _{CC} = 1.1 V		1.1	
	Low lovel output ourrent	$V_{CC} = 1.4 \text{ V}$		1.7	ı
I _{OL}	Low-level output current	V _{CC} = 1.65 V		1.9	mA
		$V_{CC} = 2.3 \text{ V}$		3.1	
		V _{CC} = 3 V		4	
Δt/Δν	Input transition rise or fall rate	V _{CC} = 0.8 V to 3.6 V		200	ns/V
T _A	Operating free-air temperature	·	-40	125	°C

⁽¹⁾ All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. See the TI application report *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

ELECTRICAL CHARACTERISTICS

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V _{cc}	T _A	= 25°C		$T_A = -40$ °C to	85°C	T _A = 125°C		UNIT
PARAMETER	TEST CONDITIONS		MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNII
	I _{OH} = -20 μA	0.8 V to 3.6 V	V _{CC} - 0.1			V _{CC} - 0.1		V _{CC} - 0.1		
	$I_{OH} = -1.1 \text{ mA}$	1.1 V	$0.75 \times V_{CC}$			$0.7 \times V_{CC}$		$0.7 \times V_{CC}$		
	$I_{OH} = -1.7 \text{ mA}$	1.4 V	1.11			1.03		1.03		
V _{OH}	$I_{OH} = -1.9 \text{ mA}$	1.65 V	1.32			1.3		1.3		V
	$I_{OH} = -2.3 \text{ mA}$	2.3 V	2.05			1.97		1.97		
	$I_{OH} = -3.1 \text{ mA}$	2.3 V	1.9			1.85		1.85		
	$I_{OH} = -2.7 \text{ mA}$	3 V	2.72			2.67		2.67		
	I _{OH} = -4 mA	3 V	2.6			2.55		2.55		

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ELECTRICAL CHARACTERISTICS (continued)

over recommended operating free-air temperature range (unless otherwise noted)

DADAMETED	TEST CONDITIONS	V	T _A = 25°C		T _A = -40°C	to 85°C	T _A = 125	5°C	LINUT
PARAMETER	TEST CONDITIONS	V _{CC}	MIN TYP N	IAX	MIN	MAX	MIN	0.1 0.3 × V _{CC} 0.37 0.35 0.33 0.45 0.5	UNIT
	I _{OL} = 20 μA	0.8 V to 3.6 V		0.1		0.1		0.1	
	$I_{OL} = 1.1 \text{ mA}$	1.1 V	0.3 ×	V_{CC}		$0.3 \times V_{CC}$	0	$3 \times V_{CC}$	
	$I_{OL} = 1.7 \text{ mA}$	1.4 V	(0.31		0.37		0.37	
V _{OL}	$I_{OL} = 1.9 \text{ mA}$	1.65 V	(0.31		0.35		0.35	V
	$I_{OL} = 2.3 \text{ mA}$	221/	(0.31		0.33		-	
	$I_{OL} = 3.1 \text{ mA}$	2.3 V	().44		0.45		0.45	
	I _{OL} = 2.7 mA	2.1/	().31		0.33		0.33	
	I _{OL} = 4 mA	3 V	().44		0.45		0.45	
I _I A or B input	V _I = GND to 3.6 V	0 V to 3.6 V		0.1		0.5		0.5	μΑ
I _{off}	V_I or $V_O = 0$ V to 3.6 V	0 V		0.2		0.6		0.8	μΑ
ΔI_{off}	V_I or $V_O = 0$ V to 3.6 V	0 V to 0.2 V		0.2		0.6		0.8	μΑ
I _{CC}	$V_I = GND \text{ or}$ $(V_{CC} \text{ to } 3.6 \text{ V}),$ $I_O = 0$	0.8 V to 3.6 V		0.5		0.9		1.2	μА
ΔI _{CC}	$V_I = V_{CC} - 0.6 V^{(1)},$ $I_O = 0$	3.3 V		40		50		23	μΑ
	V – V or CND	0 V	1.5						n.E
C _i	$V_I = V_{CC}$ or GND	3.6 V	1.5						pF
Co	V _O = GND	0 V	3						pF

⁽¹⁾ One input at V_{CC} – 0.6 V, other input at V_{CC} or GND.

SWITCHING CHARACTERISTICS

over recommended operating free-air temperature range, $C_L = 5 pF$ (unless otherwise noted) (see Figure 3 and Figure 4)

DADAMETED	FROM (INPUT)	TO (OUTPUT)	V _{cc}	T,	λ = 25°C		$T_A = -40^{\circ}C$ to	UNIT	
PARAMETER				MIN	TYP	MAX	MIN	MAX	UNIT
		Y	0.8 V		18				
			1.2 V ± 0.1 V	2.6	7.3	12.8	2.1	15.6	ns
4	A or B		1.5 V ± 0.1 V	1.4	5.2	8.7	0.9	10.3	
t_{pd}	AUID		1.8 V ± 0.15 V	1	4.2	6.6	0.5	8.2	
			2.5 V ± 0.2 V	1	3	4.4	0.5	5.5	
			3.3 V ± 0.3 V	1	2.4	3.5	0.5	4.3	

SWITCHING CHARACTERISTICS

over recommended operating free-air temperature range, $C_L = 10 \text{ pF}$ (unless otherwise noted) (see Figure 3 and Figure 4)

PARAMETER	FROM	TO (OUTPUT)	V _{cc}	T,	_λ = 25°C		$T_A = -40^{\circ}C$ to	UNIT	
PARAMETER	(INPUT)			MIN	TYP	MAX	MIN	MAX	ONIT
			0.8 V		21				
		Y	1.2 V ± 0.1 V	1.5	8.5	14.7	1	17.2	ns
	A or B		1.5 V ± 0.1 V	1	6.2	10	0.5	11.3	
t _{pd}	AUID		1.8 V ± 0.15 V	1	5	7.7	0.5	9	
			2.5 V ± 0.2 V	1	3.6	5.2	0.5	6.1	
			3.3 V ± 0.3 V	1	2.9	4.2	0.5	4.7	

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SWITCHING CHARACTERISTICS

over recommended operating free-air temperature range, $C_L = 15 \text{ pF}$ (unless otherwise noted) (see Figure 3 and Figure 4)

DADAMETED	FROM	то	V	$T_A = 25$ °C			$T_A = -40^{\circ}C$ to	85°C	UNIT
PARAMETER	(INPUT)	(OUTPUT)	V _{cc}	MIN	TYP	MAX	MIN	MAX	UNII
		Y	0.8 V		24				
			1.2 V ± 0.1 V	3.6	9.9	16.3	3.1	19.9	
	A D		1.5 V ± 0.1 V	2.3	7.2	11.1	1.8	13.2	
t _{pd}	A or B		1.8 V ± 0.15 V	1.6	5.8	8.7	1.1	10.6	ns
		2.5 V ± 0.2 V	1	4.3	5.9	0.5	7.3		
			3.3 V ± 0.3 V	1	3.4	4.8	0.5	5.9	

SWITCHING CHARACTERISTICS

over recommended operating free-air temperature range, C_L = 30 pF (unless otherwise noted) (see Figure 3 and Figure 4)

PARAMETER	FROM	TO (OUTPUT)	V _{cc}	$T_A = 25^{\circ}C$		$T_A = -40^{\circ}C t$	$T_A = -40$ °C to 85°C		:5°C	UNIT	
PARAMETER	(INPUT)			MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNIT
			0.8 V		32.8						
		or B Y	1.2 V ± 0.1 V	4.9	13.1	20.9	4.4	25.5	4.4	27.8	
	A or D		1.5 V ± 0.1 V	3.4	9.5	14.2	2.9	16.9	2.9	18	no
t _{pd}	AUID		1.8 V ± 0.15 V	2.5	7.7	11	2	13.5	2	19.7	ns
			2.5 V ± 0.2 V	1.8	5.7	7.6	1.3	9.4	1.3	11	
			3.3 V ± 0.3 V	1.5	4.7	6.2	1	7.5	1	8.7	

OPERATING CHARACTERISTICS

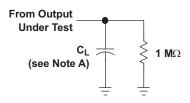
 $T_{\Delta} = 25^{\circ}C$

	PARAMETER	TEST CONDITIONS	V _{cc}	TYP	UNIT
			0.8 V	4	
			1.2 V ± 0.1 V	4	- pF
_	Davies discination associations	(40 MH-	1.5 V ± 0.1 V	4	
C_{pd}	Power dissipation capacitance	f = 10 MHz	1.8 V ± 0.15 V	4	
			2.5 V ± 0.2 V	4.1	
			3.3 V ± 0.3 V	4.3	

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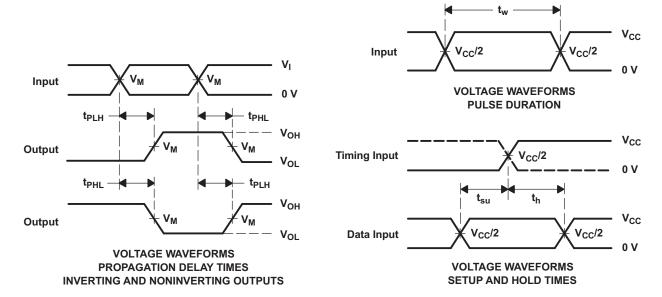
PARAMETER MEASUREMENT INFORMATION (Propagation Delays, Setup and Hold Times, and Pulse Duration)



LOAD CIRCUIT

 T_{Δ} = -25°C to 85°C

	V _{CC} = 0.8 V	V _{CC} = 1.2 V ± 0.1 V	V _{CC} = 1.5 V ± 0.1 V	V _{CC} = 1.8 V ± 0.15 V	V _{CC} = 2.5 V ± 0.2 V	V _{CC} = 3.3 V ± 0.3 V
C _L	5, 10, 15, 30 pF	5, 10, 15, 30 pF	5, 10, 15, 30 pF	5, 10, 15, 30 pF	5, 10, 15, 30 pF	5, 10, 15, 30 pF
V _M	V _{CC} /2	V _{CC} /2	V _{CC} /2	V _{CC} /2	V _{CC} /2	V _{CC} /2
V _I	V _{CC}	V _{CC}	V _{CC}	V _{CC}	V _{CC}	V _{CC}



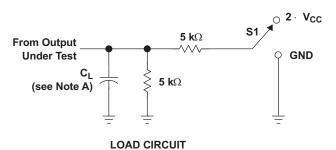
NOTES: A. C_L includes probe and jig capacitance.

- B. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_0 = 50 \Omega$, slew rate \geq 1 V/ns.
- C. The outputs are measured one at a time, with one transition per measurement.
- D. t_{PLH} and t_{PHL} are the same as t_{pd} .
- E. All parameters and waveforms are not applicable to all devices.

Figure 3. Load Circuit and Voltage Waveforms



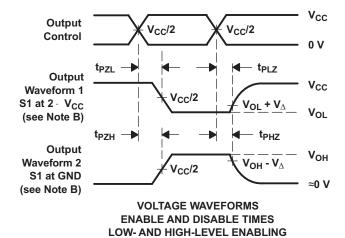
PARAMETER MEASUREMENT INFORMATION (Enable and Disable Times)



TEST	S1
t _{PLZ} /t _{PZL}	2 · V _{CC}
t _{PHZ} /t _{PZH}	GND

 $T_{A} = -25^{\circ}C \text{ to } 85^{\circ}C$

	V _{CC} = 0.8 V	V _{CC} = 1.2 V ± 0.1 V	V _{CC} = 1.5 V ± 0.1 V	V _{CC} = 1.8 V ± 0.15 V	V_{CC} = 2.5 V \pm 0.2 V	V _{CC} = 3.3 V ± 0.3 V
CL	5, 10, 15, 30 pF	5, 10, 15, 30 pF	5, 10, 15, 30 pF	5, 10, 15, 30 pF	5, 10, 15, 30 pF	5, 10, 15, 30 pF
\mathbf{v}_{M}	V _{CC} /2	V _{CC} /2	V _{CC} /2	V _{CC} /2	V _{CC} /2	V _{CC} /2
VI	V _{CC}	V _{CC}	V _{CC}	V _{CC}	V _{CC}	V _{CC}
$oldsymbol{V}_{\!\Delta}$	0.1 V	0.1 V	0.1 V	0.15 V	0.15 V	0.3 V



NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_0 = 50 \Omega$, slew rate \geq 1 V/ns.
- D. The outputs are measured one at a time, with one transition per measurement.
- E. t_{PLZ} and t_{PHZ} are the same as t_{dis} .
- F. t_{PZL} and t_{PZH} are the same as t_{en}.
- G. All parameters and waveforms are not applicable to all devices.

Figure 4. Load Circuit and Voltage Waveforms

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PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
							(6)				
SN74AUP1G08QDCKRQ1	ACTIVE	SC70	DCK	5	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	(SIJ, SIT)	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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OTHER QUALIFIED VERSIONS OF SN74AUP1G08-Q1:

PACKAGE OPTION ADDENDUM

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• Catalog : SN74AUP1G08

NOTE: Qualified Version Definitions:

• Catalog - TI's standard catalog product

PACKAGE MATERIALS INFORMATION

www.ti.com 3-Jun-2022

TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	_	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74AUP1G08QDCKRQ1	SC70	DCK	5	3000	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3

PACKAGE MATERIALS INFORMATION

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*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74AUP1G08QDCKRQ1	SC70	DCK	5	3000	190.0	190.0	30.0



SMALL OUTLINE TRANSISTOR



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. Reference JEDEC MO-203.

- 4. Support pin may differ or may not be present.
- 5. Lead width does not comply with JEDEC.
- 6. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25mm per side



SMALL OUTLINE TRANSISTOR



NOTES: (continued)

7. Publication IPC-7351 may have alternate designs.8. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)

- 9. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 10. Board assembly site may have different recommendations for stencil design.



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